

GaAlAs T-1 3/4 PACKAGE INFRARED EMITTING DIODE

MIE-534L3

Description

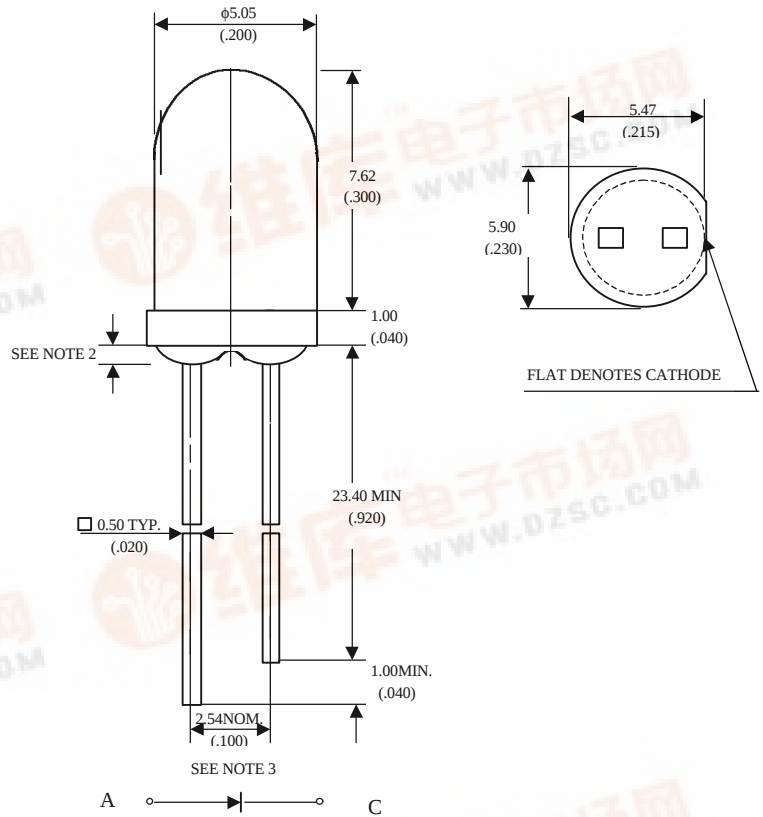
The MIE-534L3 is an infrared emitting diode in GaAlAs on GaAlAs technology molded in water clear plastic package .

Features

- Suitable for DC and high pulse current operation
- Standard T-1 3/4 ($\phi 5\text{mm}$) package
- Peak wavelength $\lambda_p = 880\text{ nm}$
- Good spectral matching to si-photodetector
- Radiation angle : 30°

Package Dimensions

Unite: mm (inches)



NOTES :

1. Tolerance is $\pm 0.25\text{ mm}$ (.010") unless otherwise noted.
2. Protruded resin under flange is 1.5 mm (.059") max.
3. Lead spacing is measured where the leads emerge from the package.

Absolute Maximum Ratings

'@ $T_A = 25^\circ\text{C}$

Parameter	Maximum Rating	Unit
Power Dissipation	120	mW
Peak Forward Current(300pps,10 μs pulse	1	A
Continuos Forward Current	100	mA
Reverse Voltage	5	V
Operating Temperature Range	-55°C to $+100^\circ\text{C}$	
Storage Temperature Range	-55°C to $+100^\circ\text{C}$	
Lead Soldering Temperature	260°C for 5 seconds	

Optical-Electrical Characteristics

@ $T_A = 25^\circ\text{C}$

Parameter	Test Conditions	Symbol	Min.	Typ.	Max.	Unit
Radiant Intensity	$I_F = 20\text{mA}$	I_e		2.8		mW/sr
Forward Voltage	$I_F = 50\text{mA}$	V_F		1.4	1.7	V
Reverse Current	$V_R = 5\text{V}$	I_R			100	μA
Peak Wavelength	$I_F = 20\text{mA}$	λ_p		880		nm
Spectral Bandwidth	$I_F = 20\text{mA}$	$\Delta\lambda$		80		nm
Half View Angle	$I_F = 20\text{mA}$	$2\theta_{1/2}$		30		deg.

Typical Optical-Electrical Characteristic Curves

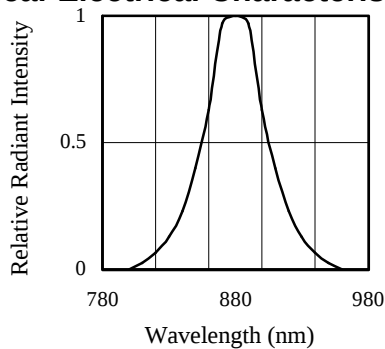


FIG.1 SPECTRAL DISTRIBUTION

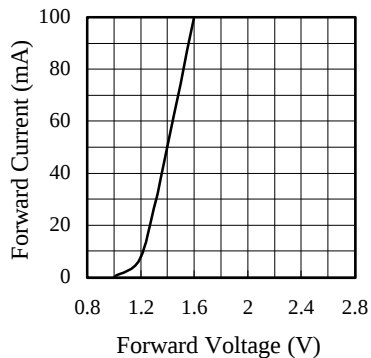


FIG.3 FORWARD CURRENT VS. FORWARD VOLTAGE

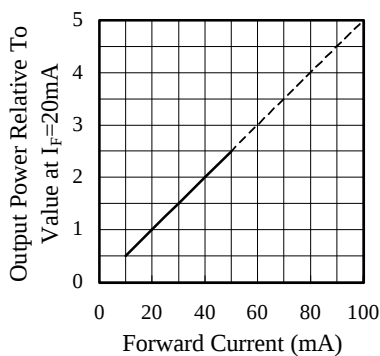


FIG.5 RELATIVE RADIANT INTENSITY VS. FORWARD CURRENT

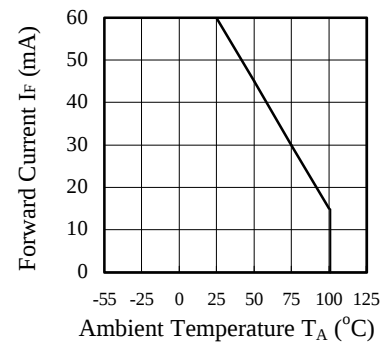


FIG.2 FORWARD CURRENT VS. AMBIENT TEMPERATURE

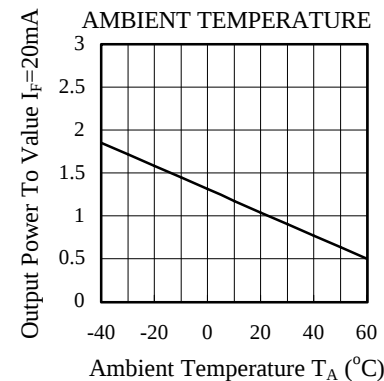


FIG.4 RELATIVE RADIANT INTENSITY VS. AMBIENT TEMPERATURE

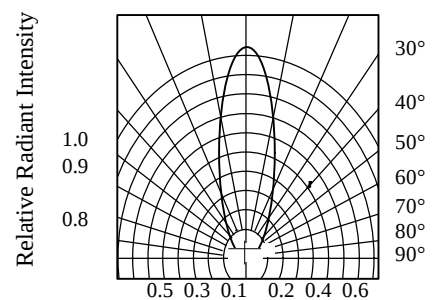


FIG.5 RADIATION DIAGRAM